

IN THE CLAIMS

1 (Previously Presented). A method comprising:
exposing an implanted wafer to an infrared laser; and
exposing said implanted semiconductor wafer to a second laser at an energy lower
than the energy of said infrared laser.

2 (Withdrawn). The method of claim 1 including exposing an implanted wafer to
acoustic energy to activate the implanted species using a mechanical vibration source.

3 (Withdrawn). The method of claim 2 including using a piezoelectric generator.

4 (Original). The method of claim 1 including generating acoustic energy using a laser
beam.

5 (Original). The method of claim 1 including exposing the implanted wafer to acoustic
energy while heating the wafer.

Claims 6 and 7 (Canceled).

8 (Withdrawn). The method of claim 5 wherein heating the wafer includes
exposing the wafer to rapid thermal anneal lamps.

9 (Original). The method of claim 1 including exposing the wafer to two laser beams,
said laser beams having different energy, one of said laser beams to heat said wafer and the other
of said laser beams to generate phonons.

10 (Original). The method of claim 1 including annealing the wafer after ion
implantation and subsequently using acoustic energy to activate the implanted species by the
generation of phonons.

Claim 11 (Canceled).

12 (Withdrawn). The method of claim 11 including using a piezoelectric transducer to perturb said wafer.

13 (Withdrawn). The method of claim 12 including using a transducer mounted in a wafer holder to perturb said wafer.

Claim 14 (Canceled).

15 (Withdrawn). The method of claim 14 including applying heat using rapid thermal annealing lamps.

Claims 16-18 (Canceled).

19 (Withdrawn). The method of claim 18 including mechanically perturbing said wafer in a rapid thermal annealing furnace.

20 (Withdrawn). The method of claim 14 including heating said wafer and then mechanically perturbing said wafer.

21 (Previously Presented). A method comprising:

exposing an implanted semiconductor wafer to a first laser at a first energy to heat said wafer to a temperature in excessive of 1000°C; and

exposing said implanted semiconductor wafer to a second laser at a second energy lower than said first energy to heat said wafer to a temperature less than 1000°C.

22 (Original). The method of claim 21 including exposing said semiconductor wafer to said second laser to generate acoustical energy.

23 (Original). The method of claim 22 including generating acoustical energy to activate implanted species.

24 (Original). The method of claim 21 including exposing said semiconductor wafer to said first laser that is a infrared laser.

25 (Original). The method of claim 21 including heating said wafer to activate said species.